

# IRLML5203GPbF

HEXFET® Power MOSFET

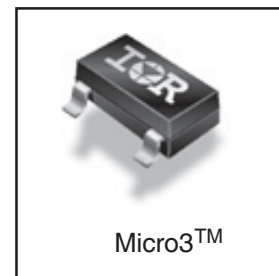
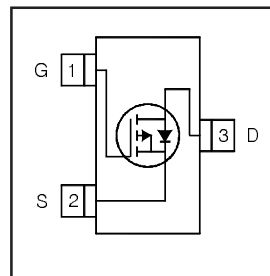
- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- Low Gate Charge
- Lead-Free
- Halogen-Free

$V_{DSS}$	$R_{DS(on)}$ max (m $\Omega$ )	$I_D$
<b>-30V</b>	98 @ $V_{GS} = -10V$	-3.0A
	165 @ $V_{GS} = -4.5V$	-2.6A

## Description

These P-channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain- Source Voltage	-30	V
$I_D$ @ $T_A = 25^\circ C$	Continuous Drain Current, $V_{GS}$ @ -10V	-3.0	A
$I_D$ @ $T_A = 70^\circ C$	Continuous Drain Current, $V_{GS}$ @ -10V	-2.4	
$I_{DM}$	Pulsed Drain Current ①	-24	
$P_D$ @ $T_A = 25^\circ C$	Power Dissipation	1.25	W
$P_D$ @ $T_A = 70^\circ C$	Power Dissipation	0.80	
	Linear Derating Factor	10	mW/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

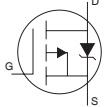
## Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ③	100	°C/W

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.019	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	98	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.0A ②
		—	—	165		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.6A ②
V <sub>GS(th)</sub>	Gate Threshold Voltage	-1.0	—	-2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
g <sub>fs</sub>	Forward Transconductance	3.1	—	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.0A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-1.0	μA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V
		—	—	-5.0		V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 70°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-100	nA	V <sub>GS</sub> = -20V
	Gate-to-Source Reverse Leakage	—	—	100		V <sub>GS</sub> = 20V
Q <sub>g</sub>	Total Gate Charge	—	9.5	14	nC	I <sub>D</sub> = -3.0A
Q <sub>gs</sub>	Gate-to-Source Charge	—	2.3	3.5		V <sub>DS</sub> = -24V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	1.6	2.4		V <sub>GS</sub> = -10V ②
t <sub>d(on)</sub>	Turn-On Delay Time	—	12	—	ns	V <sub>DD</sub> = -15V ②
t <sub>r</sub>	Rise Time	—	18	—		I <sub>D</sub> = -1.0A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	88	—		R <sub>G</sub> = 6.0Ω
t <sub>f</sub>	Fall Time	—	52	—		V <sub>GS</sub> = -10V
C <sub>iss</sub>	Input Capacitance	—	510	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	71	—		V <sub>DS</sub> = -25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	43	—		f = 1.0MHz

## Source-Drain Ratings and Characteristics

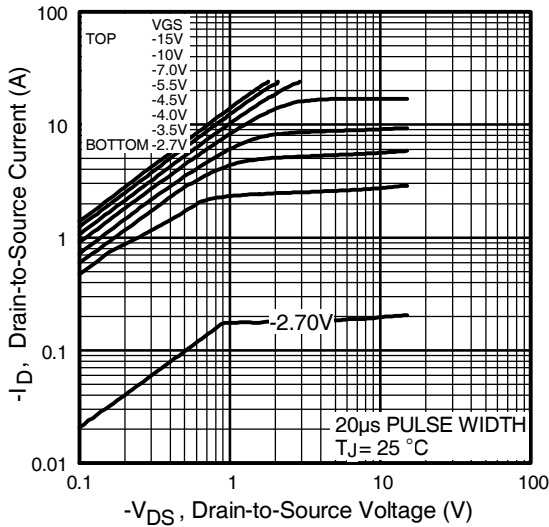
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	-24		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -1.3A, V <sub>GS</sub> = 0V ②
t <sub>rr</sub>	Reverse Recovery Time	—	17	26	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -1.3A
Q <sub>rr</sub>	Reverse Recovery Charge	—	12	18	nC	di/dt = -100A/μs ②

### Notes:

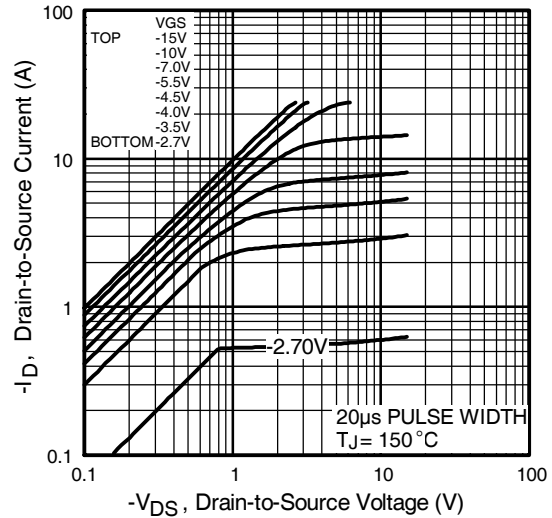
① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width ≤ 400μs; duty cycle ≤ 2%.

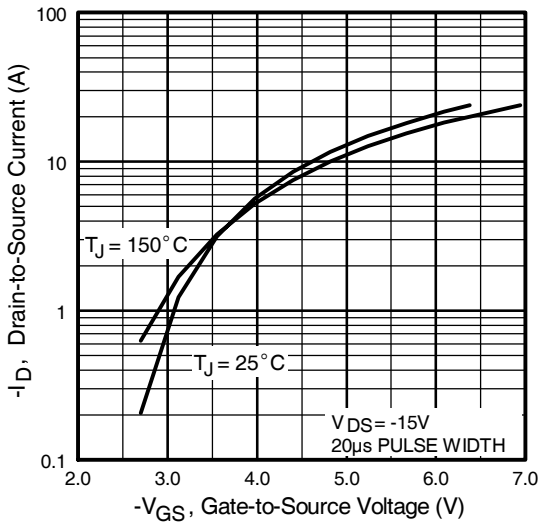
③ Surface mounted on FR-4 board, t ≤ 5sec.



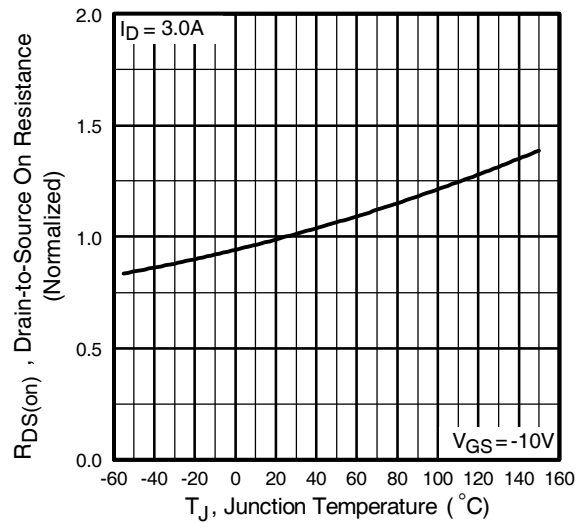
**Fig 1.** Typical Output Characteristics



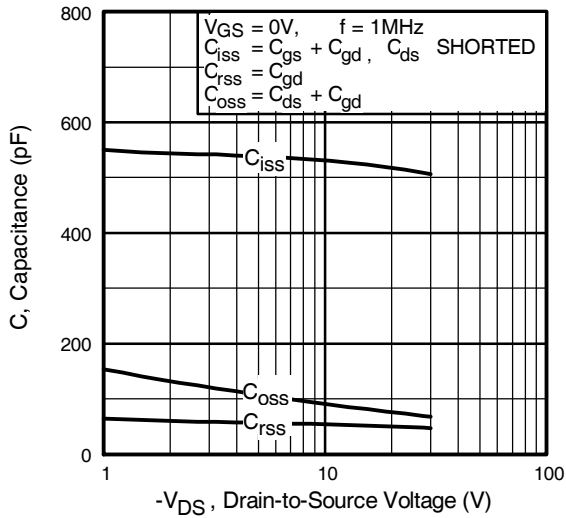
**Fig 2.** Typical Output Characteristics



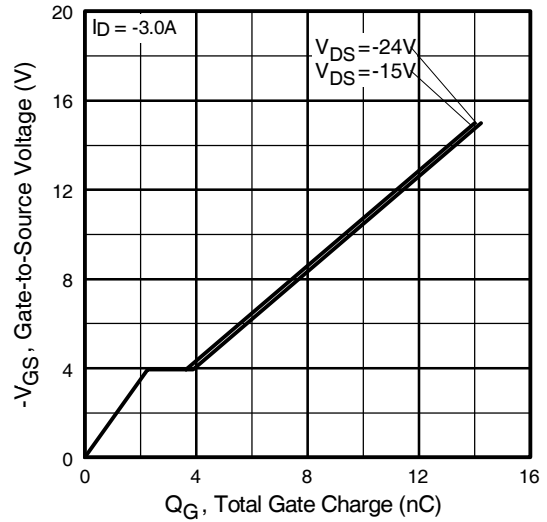
**Fig 3.** Typical Transfer Characteristics



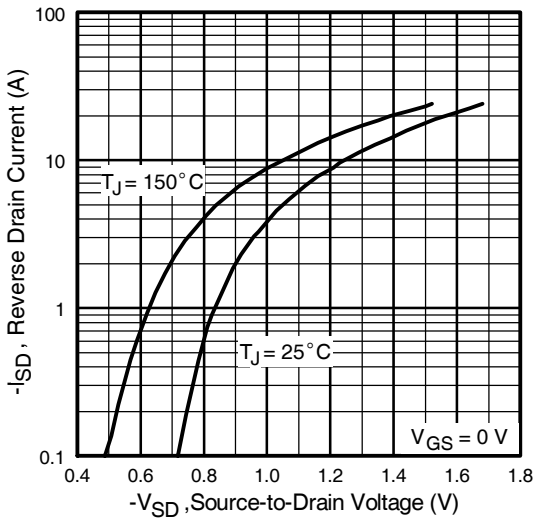
**Fig 4.** Normalized On-Resistance Vs. Temperature



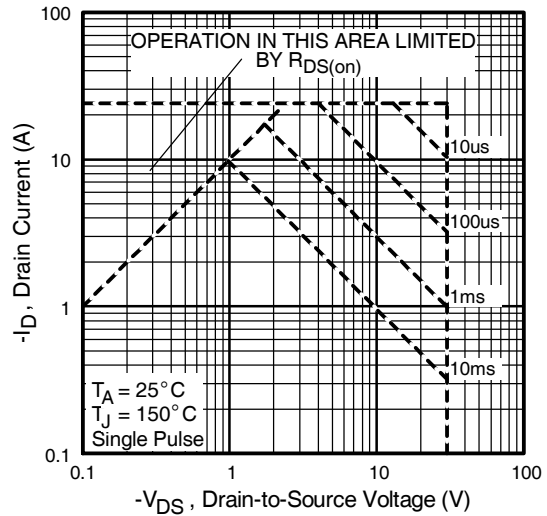
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



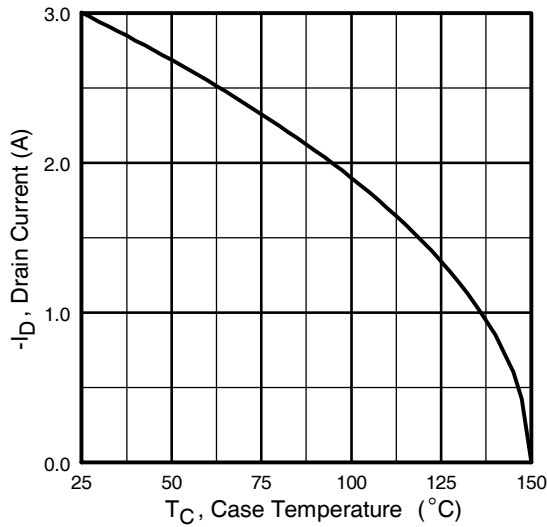
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



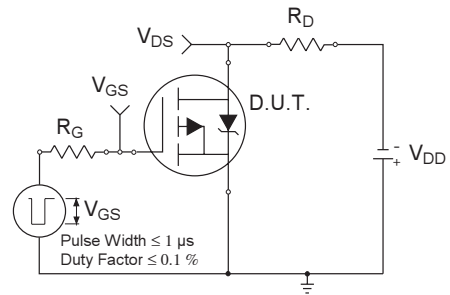
**Fig 7.** Typical Source-Drain Diode Forward Voltage



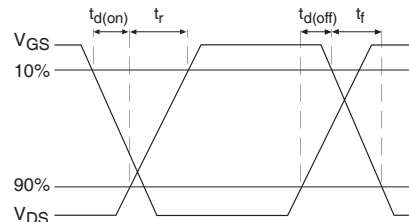
**Fig 8.** Maximum Safe Operating Area



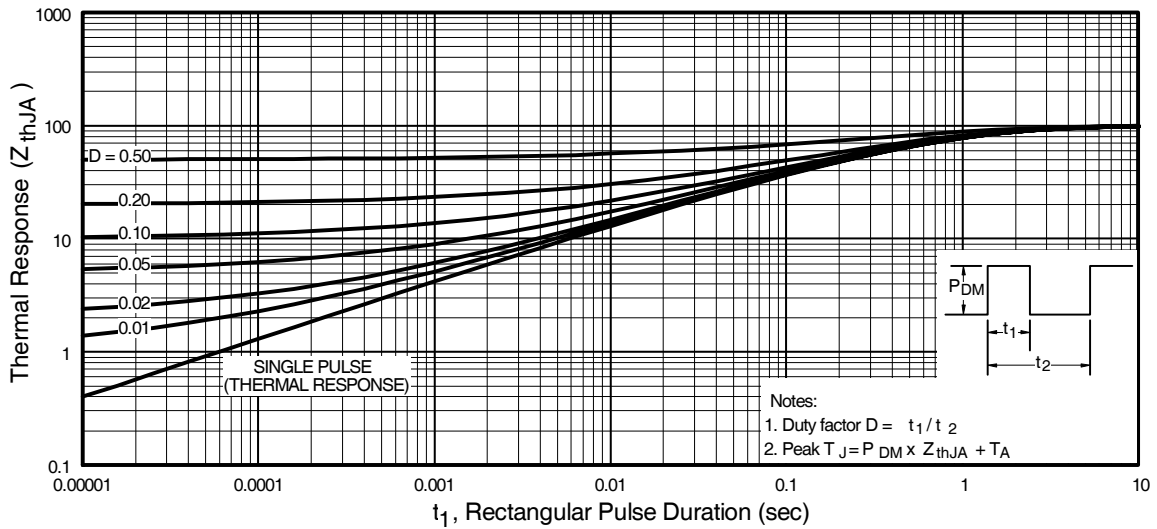
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



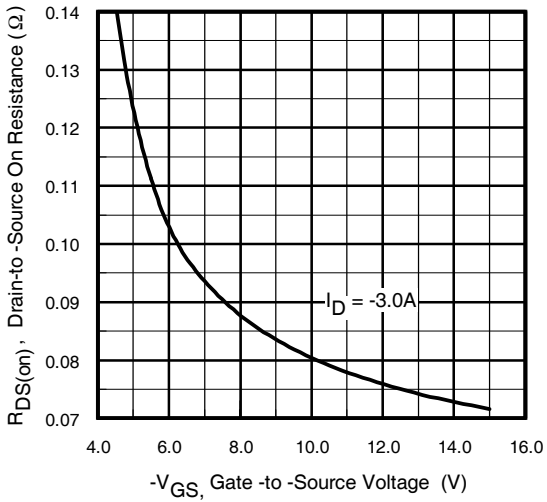
**Fig 10b.** Switching Time Waveforms



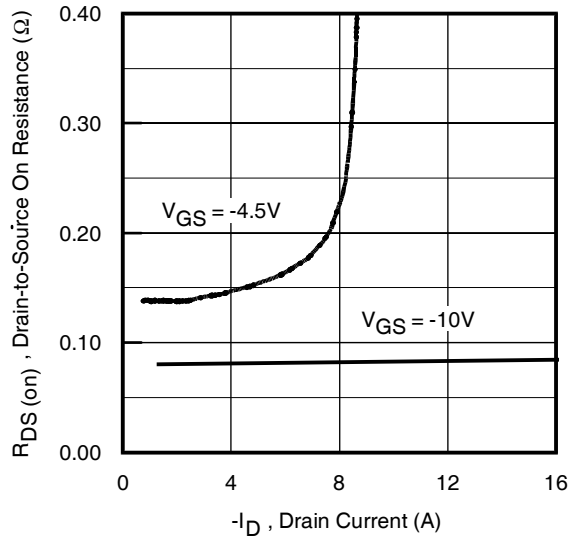
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

# IRLML5203GPbF

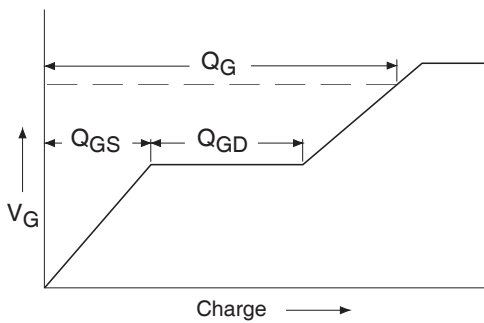
International  
**IR** Rectifier



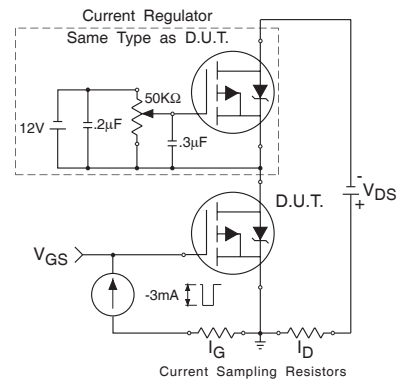
**Fig 11.** Typical On-Resistance Vs. Gate Voltage



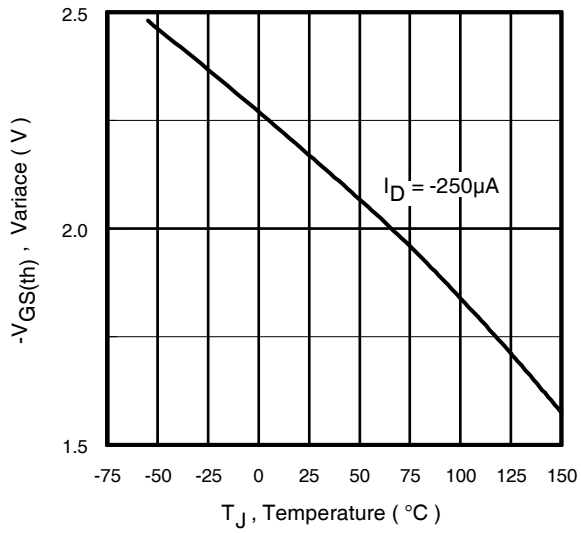
**Fig 12.** Typical On-Resistance Vs. Drain Current



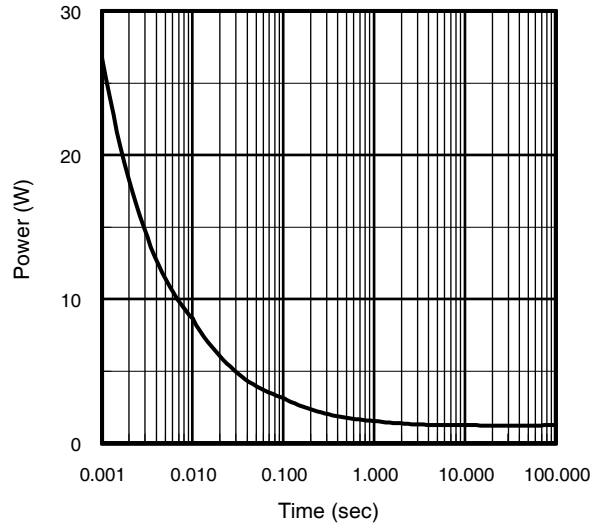
**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit



**Fig 14.** Threshold Voltage Vs. Temperature

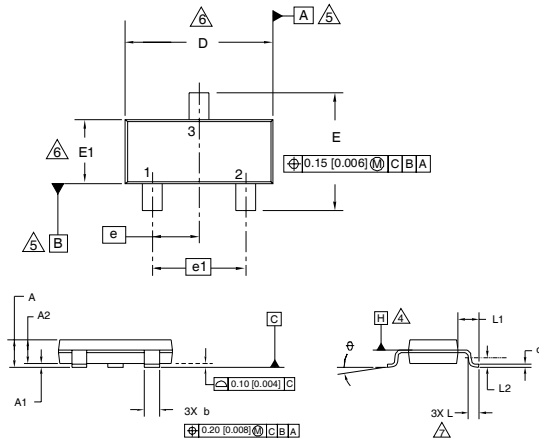


**Fig 15.** Typical Power Vs. Time

# IRLML5203GPbF

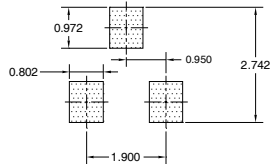
## Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



DIMENSIONS				
SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.89	1.12	0.035	0.044
A1	0.01	0.10	0.0004	0.004
A2	0.88	1.02	0.035	0.040
b	0.30	0.50	0.012	0.020
c	0.08	0.20	0.003	0.008
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E1	1.20	1.40	0.047	0.055
e	0.95	BSC	0.037	BSC
e1	1.90	BSC	0.075	BSC
L	0.40	0.60	0.016	0.024
L1	0.54	REF	0.021	REF
L2	0.25	BSC	0.010	BSC
⊕	0	8	0	8

### Recommended Footprint

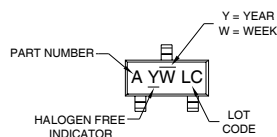


### NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. CONTROLLING DIMENSION: MILLIMETER.
4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H. DIMENSIONS DOES NOT INCLUDE MOLD PROTRUSIONS OR INTERLEAD FLASH. MOLD PROTRUSIONS OR INTERLEAD FLASH SHALL NOT EXCEED 0.25 MM (0.010 INCH) PER SIDE.
7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236 AB.

## Micro3 (SOT-23 / TO-236AB) Part Marking Information

### Micro3 / SOT-23 Package Marking



### PART NUMBER CODE REFERENCE:

- A = IRLML2402
- B = IRLML2803
- C = IRLML2402
- D = IRLML5103
- E = IRLML6402
- F = IRLML6401
- G = IRLML2502
- H = IRLML5203

Note: A line above the work week (as shown here) indicates Lead-free

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
2006	6		
2007	7		
2008	8		
2009	9		
2010	0	24	X
		25	Y
		26	Z

W = (27-52) IF PRECEDED BY A LETTER

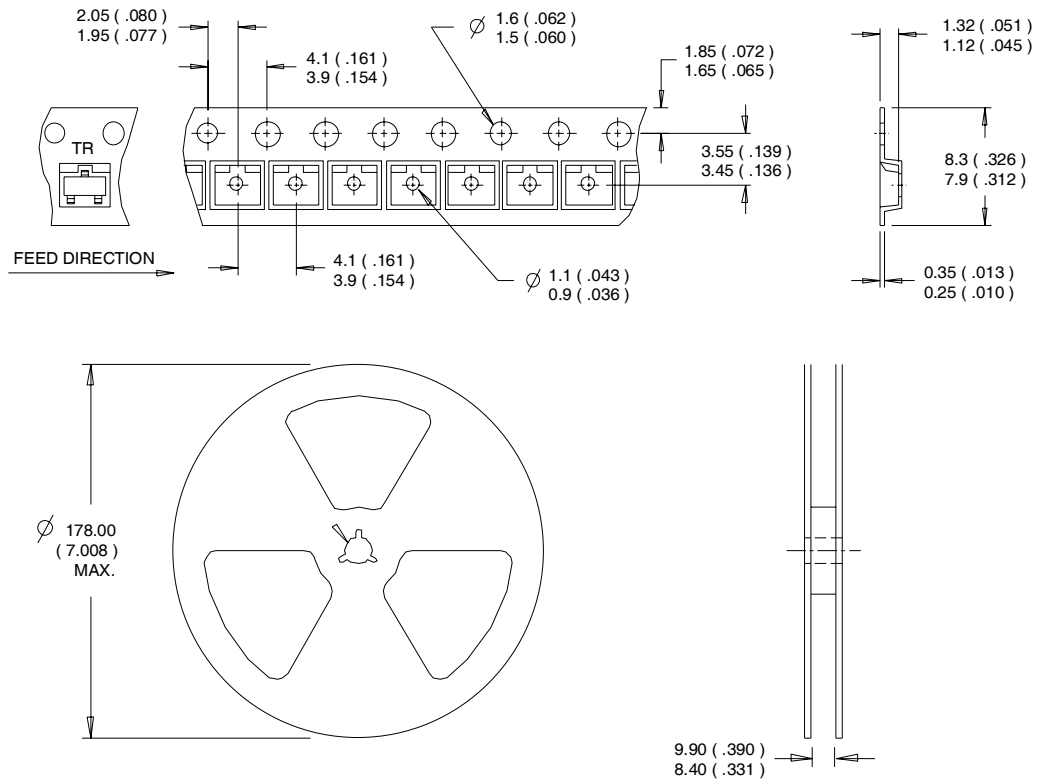
YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
2006	F		
2007	G		
2008	H		
2009	J		
2010	K	50	X
		51	Y
		52	Z

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>



## Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:  
 1. CONTROLLING DIMENSION : MILLIMETER.  
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

**Note:** For the most current drawing please refer to IR website at <http://www.irf.com/package>

Data and specifications subject to change without notice.